

NEC's LOW POWER GPS RF RECEIVER

UPB1008K

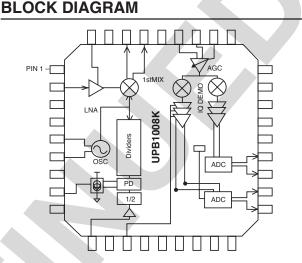
FEATURES

- LOW POWER CONSUMPTION: 52 mW
- DUAL-CONVERSION IQ DOWN CONVERTER¹: Reference frequency: REFin = 27 MHz
- PSEUDO-BASEBAND WITH 2-BIT DIGITIZED OUTPUT
- ON-CHIP LNA, ON-CHIP FREQUENCY SYNTHESIZER, IF AGC AMPLIFIER:

with 45 dB typical range of adjustable gain

SMALL 36 PIN QFN PACKAGE:
Flat lead style for better RF performance
Note:

1. Based on eRide's proprietary GPS DSP architecture



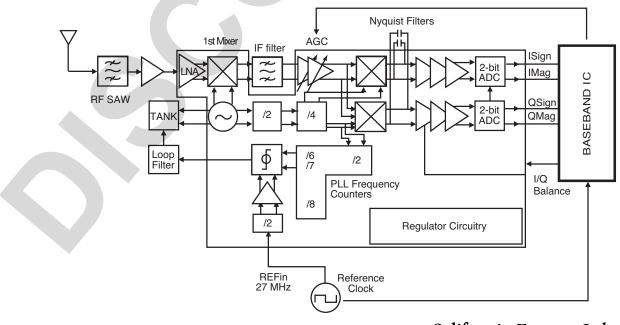
APPLICATIONS

- E911 ENABLED MOBILE PHONE
- IN-VEHICLE NAVIGATION SYSTEMS
- LOW POWER HANDHELD GPS RECEIVER
- PC/PDA+GPS INTEGRATION
- ASSET TRACKING

DESCRIPTION

NEC's UPB1008K is a Silicon RFIC especially designed for handheld low power/low cost GPS receivers. The IC combines an LNA, followed by a double-conversion RF/IF downconverter block and a PLL frequency synthesizer on one chip. The second IF Freqency is a pseudo- baseband signal into a on-chip 2-bit A/D converters. The device can operate on a supply voltage as low as 2.7 V, and is a housed in a small 36 pin QFN (Quad, Flat, No-lead) package, resulting in a very low power consumption and reduced board space.

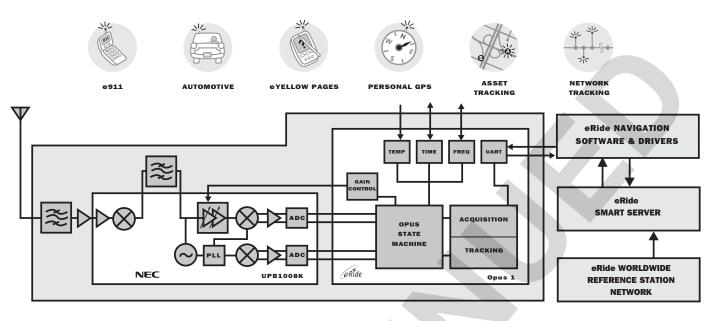
NEC's stringent quality assurance and test procedures ensure the highest reliability and performance.



RF APPLICATION DIAGRAM

California Eastern Laboratories

ADVANCED GPS COMPLETE SOLUTION



ADVANCED GPS COMPLETE SOLUTION

"NEC Corporation and eRide, Inc. have teamed to provide an advanced positioning solution delivering high GPS performance, accuracy, integration and architecture flexibility. The chip set combines CEL's **UPB1008K** receiver IC with eRide's **Opus One** SOC (System-on-a-Chip) Baseband ASIC and is suitable for standard GPS products as well as Cellular Handset applications. Also provided are scalable client navigation software and drivers, plus location-aiding data from eRide's Smart Server. Together, they offer a complete hardware/infrastructure solution.

The chip set's design allows it to operate independently of wireless interface standards - and independently of the host product's CPU and Operating System. This unique approach to system integration makes it easy to deploy the chip set into an wireless application, in any wireless network. A "Universal Hardware" solution, the design promises lower manufacturing costs and, ultimately lower cost to the consumer.

The chip set's advanced positioning architecture offers unmatched sensitivity providing fast, accurate positioning architecture offers unmatched sensitivity providing fast and accurate position fixes, even when indoors or in deep in urban canyons."

HIGH PERFORMANCE GPS OMNI MODE

LI, C/A code receiver		
Performance	Indoor	Outdoor
Time to First Fix w/ aiding	5-7sec	1-3sec
Time to First Fix w/o aiding	10-20sec	3-5sec
Accuracy	10-25m cep	2-5m cep
Sensitivity	-155dBm	-142dBm
	in 1sec dwells	in two 10msec dwells

Superior performance in high reflection indoor environments and in urban canyon types of outdoor environments

POWER DISSIPATION

First Fix	400 mW
Tracking	200-300 mW
Stand By	30 mW

ELECTRICAL CHARACTERISTICS (TA = 25°C, Vcc = 3.0 V, unless otherwise specified)

SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	ТҮР	MAX
lcc	Total Circuit Current, No Signals	mA	14	18	23.5
Vcc	Supply Voltage	V	2.7	3.0	3.3
ICC_PD	Power down current, PIN 13 = VIL	μΑ	-	1	10
Icc rf	RF Block Circuit Current (pin 3), No signal	μΑ	0.4	0.5	0.7
Icc lo	VCO Block Circuit Current (pin 7), No signal	mA	4.1	5.6	7.2
ICC pll	PLL Block Circuit Current (pin 9), No signal	mA	2.7	3.6	4.7
ICC bb	Baseband Block Circuit Current (pin 23), No signal,	mA	2.5	3.4	4.3
	open load				
ICC if	IF Block Circuit Current (pin 28) , No signal	mA	2.7	3.7	4.7
ICC Ina	Pre-Amplifier Open Connector Current (pin 36), No signal	mA	1.0	1.4	1.8

LNA/RF DOWNCONVERTER

(fRFin = 1575.42 MHz, f1stLOin = 1400 MHz, PLO = -10 dBm, f1stIF = 175 MHz, Pin 13: VIL = 3 V, ZL differential = 32Ω & Zs = Γopt)

SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	ТҮР	MAX
CGLNA_MIX	Power conversion gain from 2nd LNA/mixer to 1st IF, $P_{RFin} = -50 \text{ dBm}$	dB	18	23	28
NFLNA_MIX	Noise Figure of 2nd LNA/mixer(SSB), Input matched	dB	-	5	-
P1dBLNA_MIX	1 dB Compression refer to source, Input matched	dBm	-	-38	-
ZLNAin	RF Input Impedance of LNA	Ohm	-	31	-
ZMIXout	IF Output Impedance of Mixer	Ohm		32	
Alo-IF	Local Signal Leak to IF, f1stLOin=1400 MHz, PLO = 0 dBm	dBm	-	-35	-
Alo-RF	Local Signal Leak to RF, f1stL0in=1400 MHz, PL0 = 0 dBm	dBm	-	-50	-
PLL					
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	ТҮР	MAX

SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
Ісрон	PLL Charge Pump High Side Current @ VCPout = VCC/2	μΑ	-	200	-
ICPOL	PLL Charge Pump Low Side Current @ VCPout = VCC/2	μΑ	-	-200	-
fpd	Phase Comparison Frequency	MHz	-	13.5	-

CRYSTAL OSCILLATOR/REVERENCE AMPLIFIER BLOCK

SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	ТҮР	MAX
VREFin	Reference input minimum level	mVpp	50	200	-
fref	Input Frequency of Reference Input	MHz	_	27	-
VT	VCO Control Voltage, PLL Locked	V	0.8	1.5	2.2
C/N	VCO C/N, \triangle 1kHz, Loop band width = 5 kHz	dBc/Hz	57	62	_

AGC AMPLIFIER, I-Q DEMODULATOR, and ADC BLOCK(f1stlFin = 175 MHz, Zin = 600Ω)

		- 170 Williz, Zil			
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
CGAGC/MIX	Maximum voltage conversion gain of AGC amplifier/ I-Q mixer, Pin = -60 dBm, VAGC = 0.5 V, Unmatched	dB	-	30	-
	Minimum voltage conversion gain of AGC amplifier/ I-Q mixer, Pin = -60 dBm, VAGC = 2.0 V, Unmatched	dB	_	-15	-
AAGC/MIX	AGC control range, VAGC = 0.5 V to 2 V	dB	25	45	-
P1dBAGC	1 dB compression input to AGC amplifier, set voltage gain = 30 dB	dBm	-	-45	-
VAGC	AGC control voltage	V	0.5	-	2.0
BW	3dB Mixer Bandwidth	MHz	_	10	-
Viq-c	IQ BalanceControl Voltage, Gain(Ich) = Gain (Qch)	V	_	2.1	2.8
AlQ-C	IQ Balance Control Gain Range, VIQ-C = 0 to 3 V	dB	4.0	6.5	-
Duty Ich	Ich Mag Bit Output Pulse Duty, P1stIFin = -84 dBm VAGC = 0.5 V, VIQ-C = 0 V	%	50	_	_
Duty Qch	Qch Mag Bit Output Pulse Duty, PIF2in = -88 dBm VAGC = 0.5 V, VIQ-C = 0 V	%	50	_	-
BASEBA	ND AMPLIFIER BLOCK (Zs = $2k\Omega \& ZL = 2 k\Omega$)				
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
Vввон	Baseband output logic high, CL = 10 pF	V	2.0	-	-
VBBOL	Baseband output logic low, CL = 10 pF	V	0	-	0.5

ABSOLUTE MAXIMUM RATINGS^{1,2} (TA = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
Vcc	Supply Voltage ⁴	Vcc	3.6
PD	Total Power Dissipation ³	mW	361
Тор	Operating Temperature	°C	-40 to +85
Tstg	Storage Temperature	°C	-55 to +150
ICC_total	Total Circuit Current ⁴		

Notes:

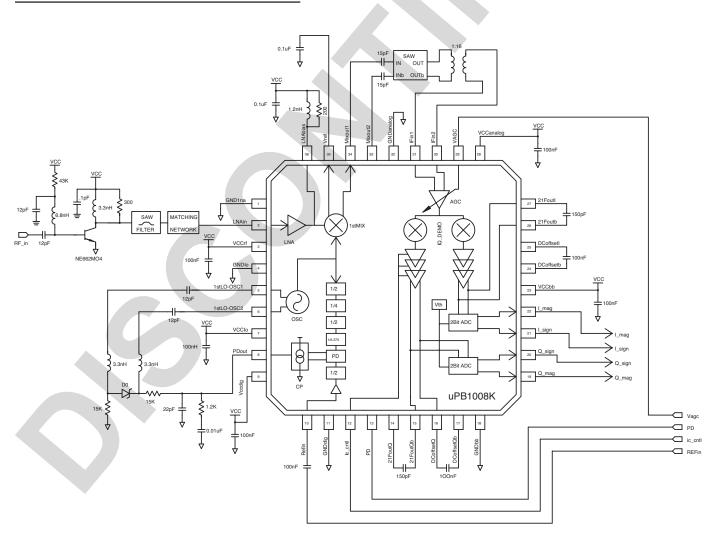
1. Operation in excess of any one of these parameters may result in permanent damage.

- 2. More than two items must not be reached simultaneously.
- 3. TA = $+85^{\circ}$ C, mounted on a 50 x 50 x 1.6 mm double-sided copper clad epoxy glass PWB.
- 4. TA = 25°C

RECOMMENDED OPERATING CONDITIONS

SYMBOLS	PARAMETERS	UNITS	MIN	TYP	MAX
Vcc	Supply Voltage	V	2.7	3.0	3.3
Тор	Operating Temperature	°C	-40	+25	+85
fRFin	RF Input Frequency	MHz		1575	
fREFin	Reference Frequency	MHz		27	
f1st∟o	1st LO Oscillating				
	Frequency	MHz		1400	
f 1stIFin	1st IF Input Frequency	MHz		175	
f2ndLOin	2nd LO Input Frequency	MHz		175	
Vін	Power Down Control				
	Voltage "High"	V	2		Vcc
VIL	Power Down Control				
	Voltage "Low"	V	0		0.5

APPLICATION CIRCUIT



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Pin No.	Symbol	Function and Application	Internal Equivalent Circuit
1	GNDIna	Ground pin of LNA	
2	LNAin	Input pin of low noise amplifier. It is a single-ended open collector design. Capacitive coupling is required; external matching will improve gain or NF.	
3	VCCrf	Supply voltage pin of LNA, RF mixer and VCO voltage regulator.	70
4	GNDlo	Ground pin of 1st LO Oscillator circuit and RF Mixer.	3 0 r=200 € a, a, ≤ r=200
5	1stLO-OSC1	Pin 5 % 6 are been nine of the differential	r=300 ♣ ♣ ♣ ♣ ≸ r=300
5 6	1stLO-OSC1	Pin 5 & 6 are base pins of the differential amplifier for 1st LO oscillator. These pins	∳ ∎ĴĬ= \$ 8
0		require an LC (varacator) tank circuit to oscillate at around 1400 MHz.	
7	VCClo	Supply voltage pin of oscillator circuit for 1st LO Oscillator and RF mixer	Regulator B GND 4 C
8	PDout	This is a current mode charge pump output. For connection to a passive RC loop filter for driving external varactor diode of 1stLO-OSC.	Source Control B-OK AESO
9	VCCdig	Supply voltage pin of digital portion of the chip.	E A Sink Control A ESD
10	REFin	Input pin of reference frequency buffer. This pin should be equipped with external 27 MHz oscillator (e.g. TCXO).	9 9 7 7 7 7 7 7 7 7 7 7
11	GNDdig	Ground pin of digital portion of the chip.	10 10 10 10 10 10 10 10 10 10

Pin No.	Symbol	Function and Application	Internal Equivalent Circuit
12	I/Q Balance Control	The voltage on this pin controls the Q channel IF Amplifier Gain. Gain control of ±2 dB can be achieved for 0~3 V. Leave open-circuited if not used. Qgain $\int_{0}^{\frac{1}{9}} \int_{0}^{\frac{1}{9}} \int_{1.5 \text{ V}}^{\frac{1}{9}} \int_{3 \text{ V}}^{\frac{1}{9}} V$	
13	PD1	Standby mode control. Low=whole chip OFF & High=Whole chip ON.	
<u>14</u> 15	2IFout-Q 2IFout-Qb	Differential ouptut pins of quadrature demodulator Q output. Adding a lowpass shunt capacitor between these pins will define the IF Bandwidth.	28 14.(27) 14.(27) 14.(27) 14.(27) 14.(27) 14.(27) 14.(27) 14.(27)
16	DC offset Q DC offset Qb	DC offset compensation pin for C arm. A low pass capacitor shunt to Pin 17 is required. DC offset compensation pin for Q-bar arm. A low pass capacitor shunt to Pin 16 is required.	

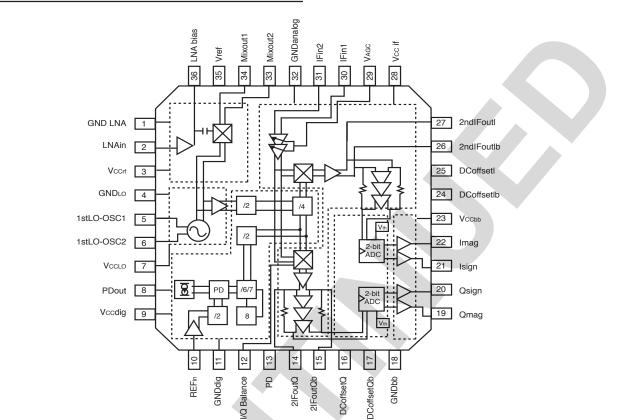
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Pin No.	Symbol	Function and Application	Internal Equivalent Circuit
10	CNDbb	Ground his of CMOS output driver	
18	GNDbb	Ground pin of CMOS output driver.	23
19	Qmag	Digitized Q signal. Magnitude bit of 2-bit ADC output.	
20	Qsign	Digitized Q signal. Sign bit of 2-bit ADC output	r=21.5
21	Isign	Digitized I signal. Sign bit of 2-bit ADC output.	
22	Imag	Digitized I signal. Magnitude bit of 2-bit ADC output.	
23	VCCbb	Supply voltage pin of CMOS output driver.	
24	DCoffsetIb	DC offset compensation pin for I-bar arm. A low pass capacitor shunt to Pin 25 is required.	See pin 16 & 17 schematic
25	DCoffsetI	DC offset compensation pin for I arm. A low pass capacitor shunt to Pin 24 is required.	
26	2IFout-Ib	Differential output pins of quadrature	See pin 14 & 15 schematic
27	2IFout-I	demodulator I output. Adding a lowpass shunt capacitor between these pins will define the IF bandwidth.	
28	VCC if	Supply voltage pin of analog portion of the chip.	
29	VAGC	Gain control voltage pin of IF amplifier. This voltage	28
		performs reverse control, (i.e., VAGC up \rightarrow gain down).	
		If this pin is left open, then it is default at	
		maximum gain.	¥
		maximum gam.	
			Å ESD Å r=300
		30	t To AGC Amp
		Typical AGC	
			29 D
		Gain Response	
		0	Å ESD Å r=3k
			- + +
		-15	320
		0.5 1.5 2 VAGC (V)	320
	15 . 4		
30	IF-in1	Differential input pins of 1st IF AGC amplifier	28
31	IF-in2		r=4k r=2k r=2k r=4k
32	GNDanalog	Ground pin of analog portion of the chip.	
			[≥] > ++ t 1 1 ″
			Regulator
			ESD ar r=4k ar ESD
			30 31
			ESD THE ESD
			32 🗗
			7.0
33	Mixout2	Differential output pins of RF mixer. This is an emitter	₃ <mark>≻−−−t≩ </mark>
34	Mixout1	follower output buffer, provide a 50 Ω output load.	
			╵ ┝ ┈┝ <mark>╶╶</mark> ┝ <mark>╴</mark> ╺┟ _┪
			[₹] ^{ζ=1.67}
			↓ c=1.67p ↓ c=111 ↓ ↓ csD

			4d
	1		

Pin No.	Symbol	Function and Application	Internal Equivalent Circuit	
35	Vref	Base-emitter junction voltage wth respect to ground. May be used for biasing an external discrete transistor. Regulation will develop PTAT current.	Regulator GND 4 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	
36	LNAbias	LNA output pin. External bias (Vcc) and matching for gain is required.	See pin 2 schematic	

INTERNAL BLOCK DIAGRAM



ORDERING INFORMATION

OUTLINE DIMENSIONS (Units in mm) Part Number Package Package Outline QFN-36 6.2±0.2 UPB1008K-A 36 Pin plastic QFN 6.0±0.2 농수수수수수수 Actual size 3.2±0.2 0HO Pin 36 Pin¹ 4 -CO.5 0.22±0.05 6 2+0 1.0 MAX 6.0+0.2 14 Caution: The island pins located on the corners are needed to fabricate products in our plant, but do not serve any other function.

Consequently the island pins should not be soldered and should remain non-connection pins.

Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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4590 Patrick Henry Drive Santa Clara, CA 95054-1817 Telephone: (408) 919-2500 Facsimile: (408) 988-0279

Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices	
Lead (Pb)	< 1000 PPM	-A Not Detected	-AZ (*)
Mercury	< 1000 PPM	Not Detected	
Cadmium	< 100 PPM	Not Detected	
Hexavalent Chromium	< 1000 PPM	Not Detected	
РВВ	< 1000 PPM	Not Detected	
PBDE	< 1000 PPM	Not Detected	

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

In no event shall CEL's liability arising out of such information exceed the total purchase price of the CEL part(s) at issue sold by CEL to customer on an annual basis.

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